
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					

FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

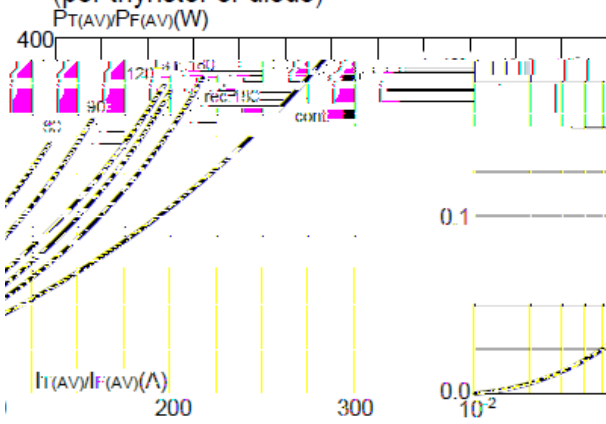


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

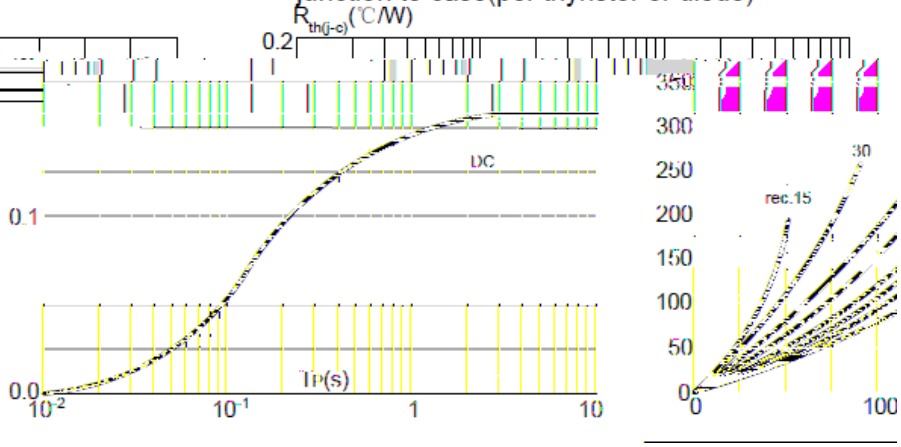


FIG.3: Forward characteristics (per thyristor or diode)

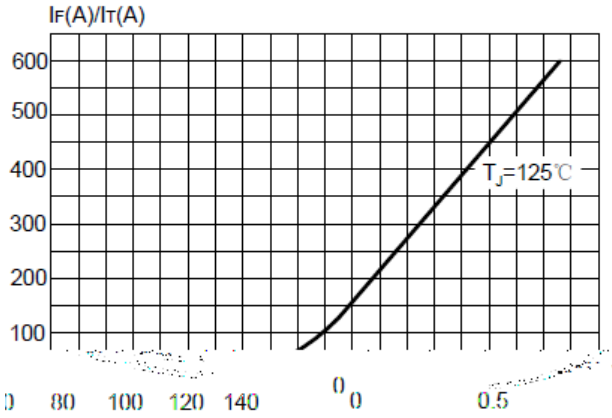


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

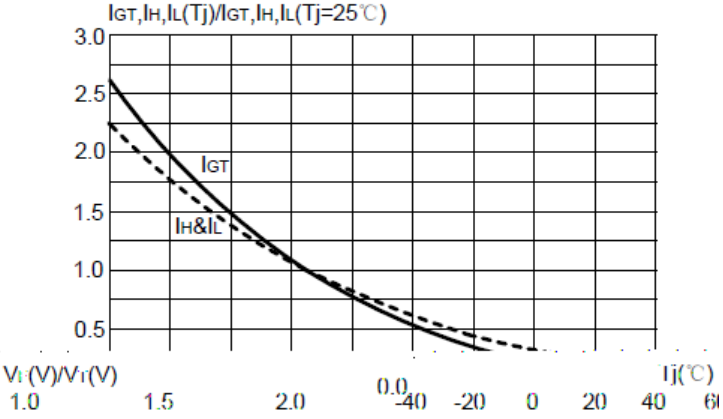
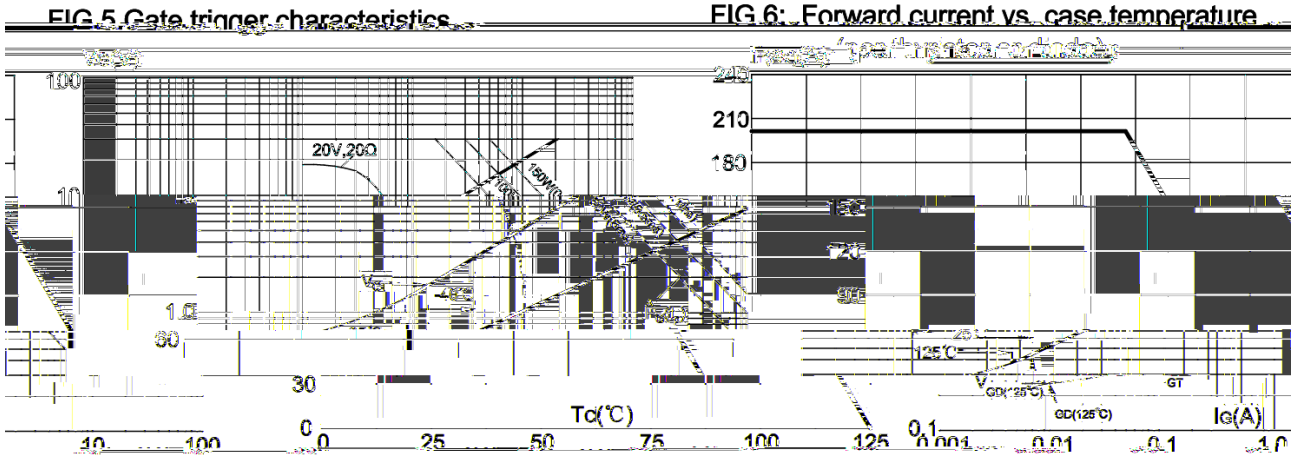
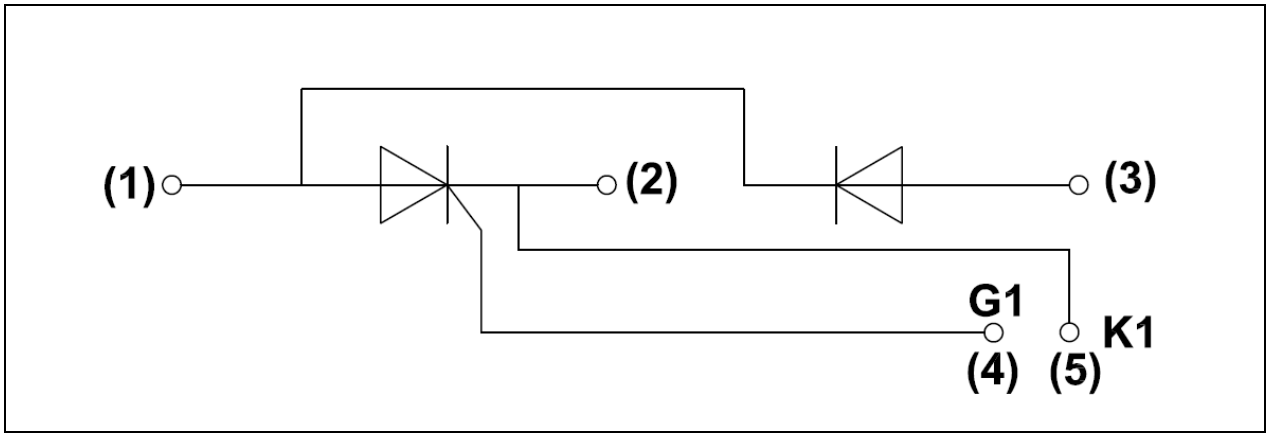
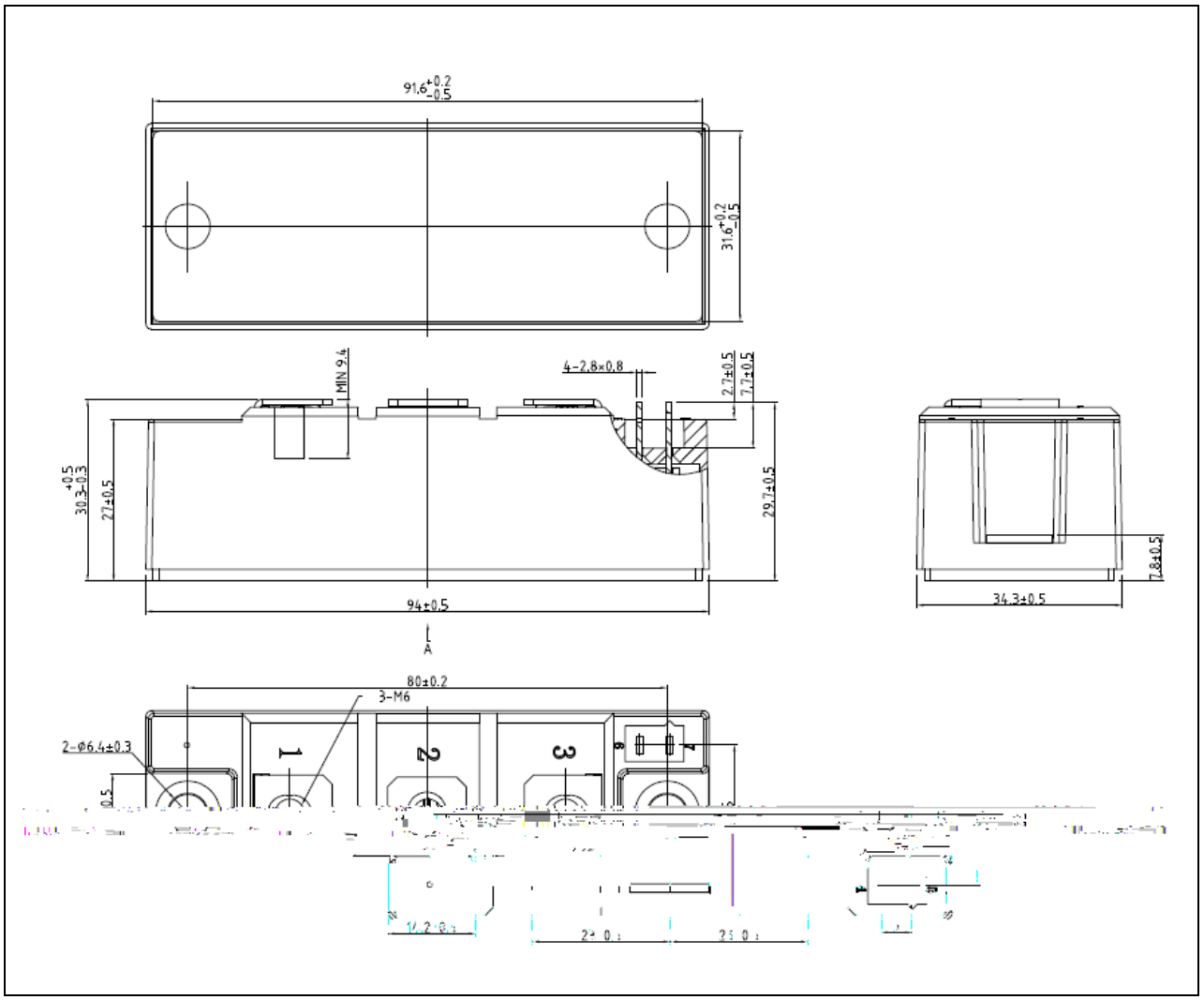


FIG.5 Gate trigger characteristics

FIG.6: Forward current vs. case temperature




(1)
(2)
(3)
G1
K1
(4)
(5)


91.6+0.2 -0.5
31.6+0.2 -0.5
MIN 9.4
4-2.8×0.8
2.7±0.5
7.7±0.5
30.3+0.5 -0.3
27±0.5
29.7±0.5
94±0.5
7.8±0.5
34.3±0.5
A
80±0.2
3-M6
2-Φ6.4±0.3
0.5
1
2
3